

# EECS150 - Digital Design

## Lecture 19 –CMOS Implementation Technologies

Oct. 31, 2013  
 Prof. Ronald Fearing  
 Electrical Engineering and Computer Sciences  
 University of California, Berkeley

(slides courtesy of Prof. John Wawrzynek)

<http://www-inst.eecs.berkeley.edu/~cs150>

## Recap and Outline

Arbiter

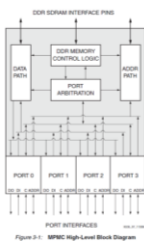
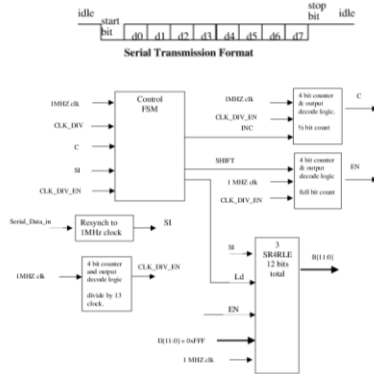


Figure 3-1: 5198C Single-Level Block Diagram

Univ. Async. Receiver



A/D Converter

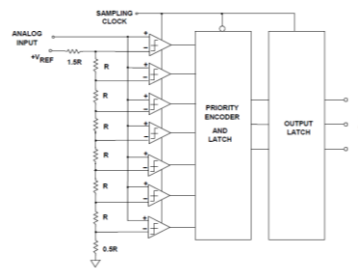


Figure 4: 3-bit All-Parallel (Flash) Converter

### Outline for Today

- Midterm 1 Feedback
  - regrade request with note to RSF by Tues Nov. 5, 5 pm.
- CMOS details

# Overview of Physical Implementations

*The stuff out of which we make systems.*

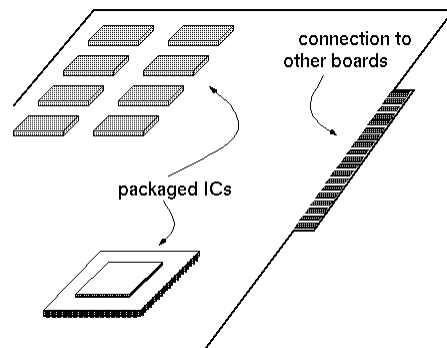
- Integrated Circuits (ICs)
  - Combinational logic circuits, memory elements, analog interfaces.
- Printed Circuits (PC) boards
  - substrate for ICs and interconnection, distribution of CLK, Vdd, and GND signals, heat dissipation.
- Power Supplies
  - Converts line AC voltage to regulated DC low voltage levels.
- Chassis (rack, card case, ...)
  - holds boards, power supply, fans, provides physical interface to user or other systems.
- Connectors and Cables.

Fall 2013

EECS150 - Lec19-CMOS

Page 3

## Printed Circuit Boards



- fiberglass or ceramic
- 1-25 conductive layers
- ~1-20in on a side
- IC packages are soldered down.

## Multichip Modules (MCMs)

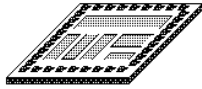
- Multiple chips directly connected to a substrate. (silicon, ceramic, plastic, fiberglass) without chip packages.

Fall 2013

EECS150 - Lec19-CMOS

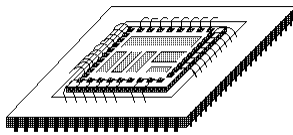
Page 4

## Integrated Circuits



- Primarily Crystalline Silicon
- 1mm - 25mm on a side
- 100 - 1000M transistors
- (25 - 250M "logic gates")
- 3 - 10 conductive layers
- 2012 - feature size  $\sim 28\text{nm} = 0.028 \times 10^{-6} \text{ m}$
- "CMOS" most common - complementary metal oxide semiconductor

### Chip in Package



- Package provides:
  - spreading of chip-level signal paths to board-level
  - heat dissipation.
- Ceramic or plastic with gold wires.

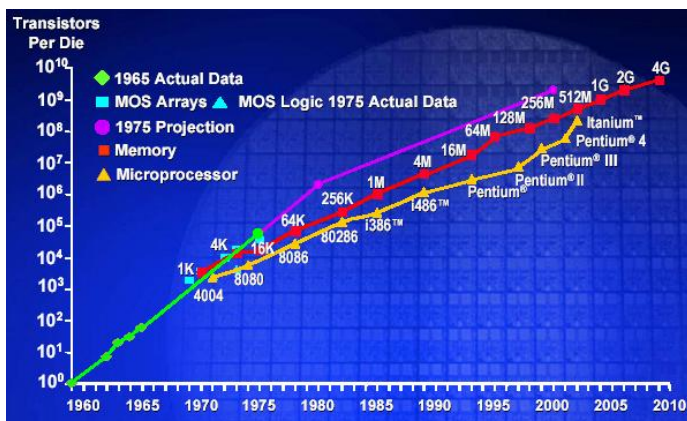
Fall 2013

EECS150 - Lec19-CMOS

Page 5

## Integrated Circuits

- Moore's Law has fueled innovation for the last 3 decades.



- "Number of transistors on a die doubles every 18 months."
- What are the consequences of Moore's law?

Fall 2013

EECS150 - Lec19-CMOS

Page 6

## Chip-level Function Implementation Alternatives

Full-custom: All circuits/transistor layouts optimized for application.

Standard-cell: Arrays of small function blocks (gates, FFs) automatically placed and routed.

Gate-array: Partially prefabricated wafers customized with metal layers.

FPGA: Prefabricated chips customized with switches and wires.

Microprocessor: Instruction set interpreter customized through software.

Domain Specific Processor: (DSP, NP, GPU).

} ASIC

What are the important metrics of comparison?

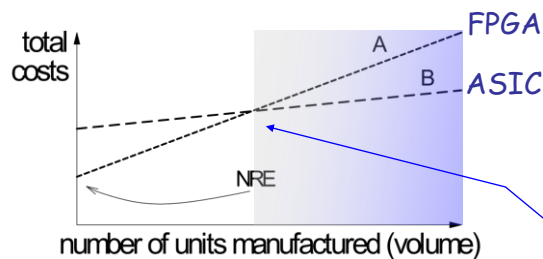
Fall 2013

EECS150 - Lec19-CMOS

Page 7

## Why FPGAs?

A tradeoff exists between NRE\* cost and manufacturing costs:



The ASIC approach is only viable for products with very high volume (where NRE could be amortized), and which were not time to market (TTM) sensitive.

Cross-over point has moved to the right (favoring FPGA) implementation as ASIC NREs have increased.

\*Non-recurring Engineering Costs

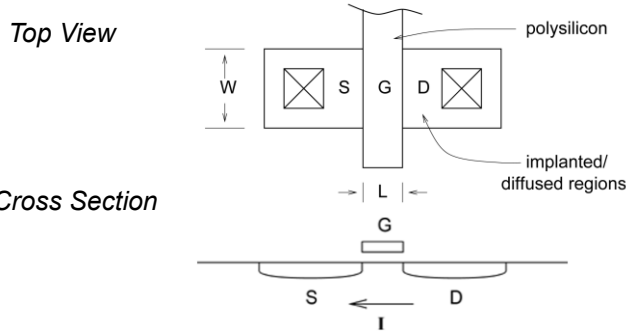
Fall 2013

EECS150 - Lec19-CMOS

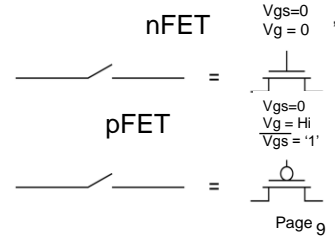
Page 8

# CMOS Devices

- MOSFET (Metal Oxide Semiconductor Field Effect Transistor).



The gate acts like a capacitor. A high voltage on the gate attracts charge into the channel. If a voltage exists between the source and drain a current will flow. In its simplest approximation, the device acts like a switch.



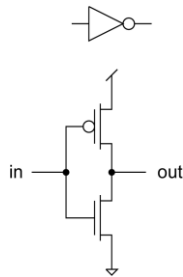
Fall 2013

EECS150 - Lec19-CMOS

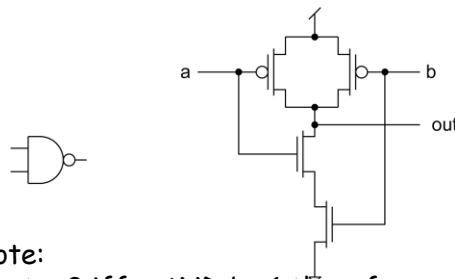
Page 9

# Transistor-level Logic Circuits

Inverter (NOT gate):



NAND gate:



Note:

• out = 0 iff a AND b = 1 therefore out = (ab)'

• pFET network and nFET networks are duals of one another.

How about AND gate?

Fall 2013

EECS150 - Lec19-CMOS

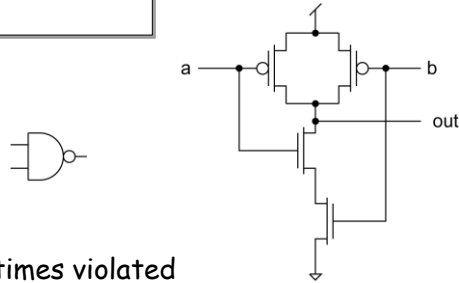
Page 10

## Transistor-level Logic Circuits

Simple rule for wiring up MOSFETs:

nFET is used only to pass logic zero.  
pFET is used only to pass logic one.

For example, consider the NAND gate:



Note: This rule is sometimes violated by expert designers under special conditions.

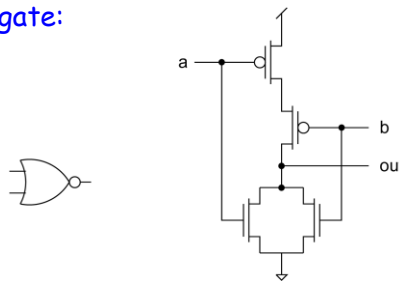
Fall 2013

EECS150 - Lec19-CMOS

Page<sub>11</sub>

## Transistor-level Logic Circuits

NOR gate:



Note:

- $\text{out} = 0$  iff  $a \text{ OR } b = 1$  therefore  $\text{out} = (a+b)'$
- Again pFET network and nFET networks are **duals** of one another.

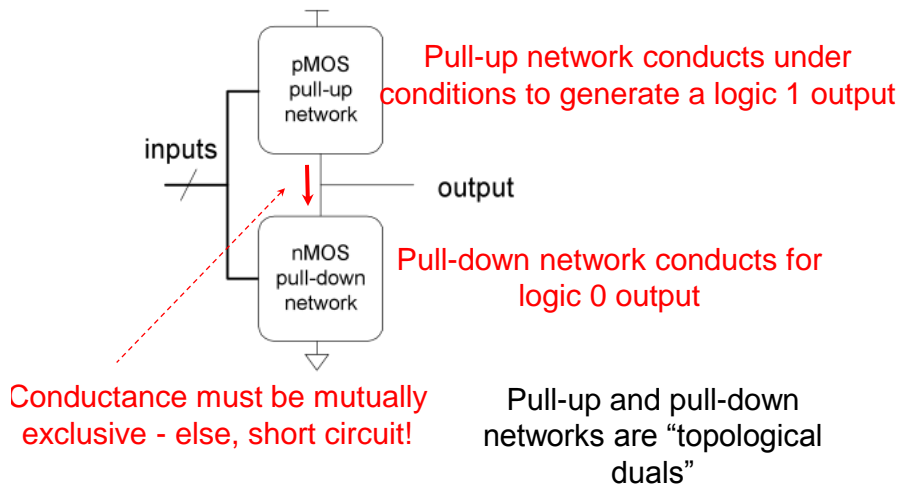
Other more complex functions are possible. Ex:  $\text{out} = (a+bc)'$

Fall 2013

EECS150 - Lec19-CMOS

Page<sub>12</sub>

## CMOS Logic Gates in General



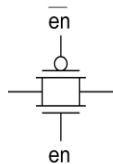
Fall 2013

EECS150 - Lec19-CMOS

Page<sub>13</sub>

## Transmission Gate

- Transmission gates are the way to build "switches" in CMOS.
- In general, both transistor types are needed:
  - nFET to pass zeros.
  - pFET to pass ones.
- The transmission gate is bi-directional (unlike logic gates).



- Does not directly connect to V<sub>dd</sub> and GND, but can be combined with logic gates or buffers to simplify many logic structures.

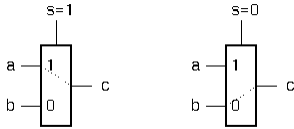
Fall 2013

EECS150 - Lec19-CMOS

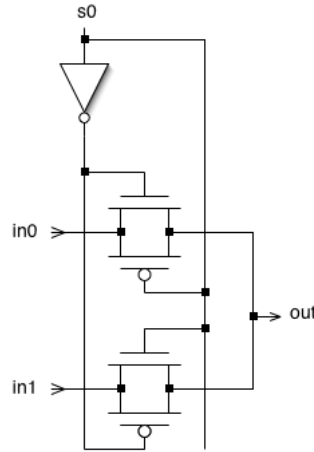
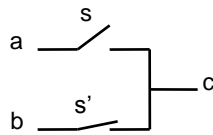
Page<sub>14</sub>

## Transmission-gate Multiplexor

2-to-multiplexor:  
 $C = sa + s'b$

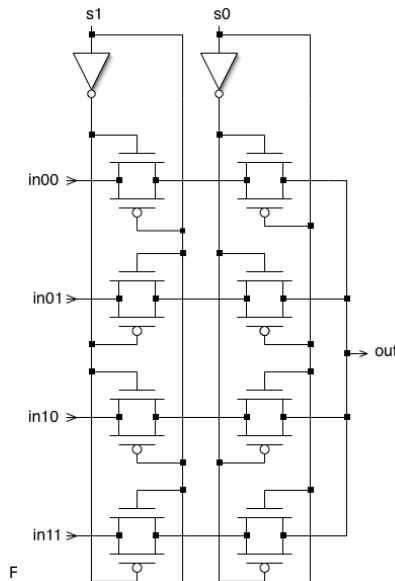


Switches simplify the implementation:



Compare the cost to logic gate implementation.

## 4-to-1 Transmission-gate Mux

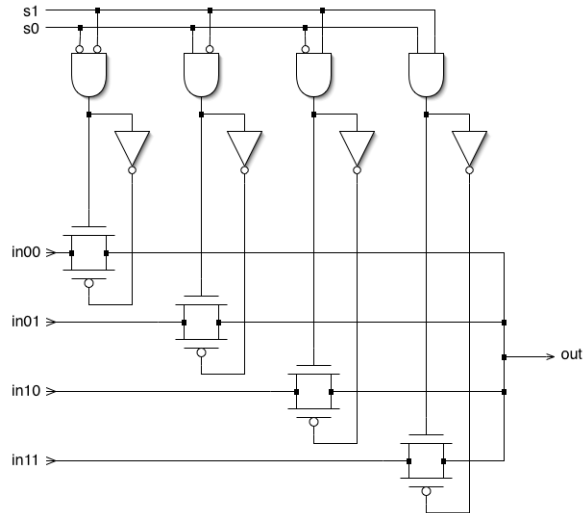


- The series connection of pass-transistors in each branch effectively forms the AND of  $s_1$  and  $s_0$  (or their complement).
- Compare cost to logic gate implementation



## Alternative 4-to-1 Multiplexor

- This version has less delay from in to out.
- In both versions, care must be taken to avoid turning on multiple paths simultaneously (shorting together the inputs).



## Tri-state Buffers

**Tri-state Buffer:**

OE	IN	OUT
0	0	Z
0	1	Z
1	0	0
1	1	1

"high impedance" (output disconnected)

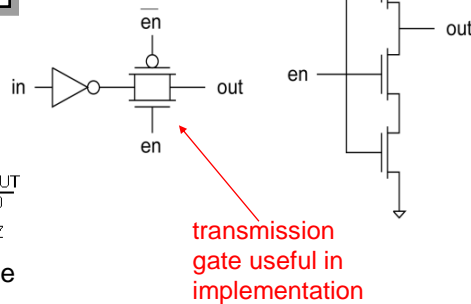
### Variations:

OE	IN	OUT
0	-	Z
1	0	1
1	1	0

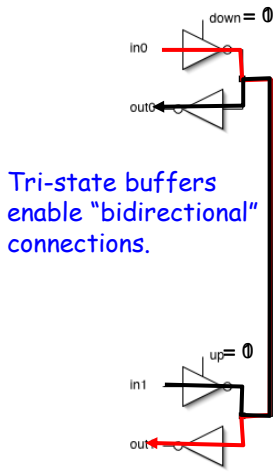
Inverting buffer

OE	IN	OUT
0	0	0
0	1	1
1	-	Z

Inverted enable

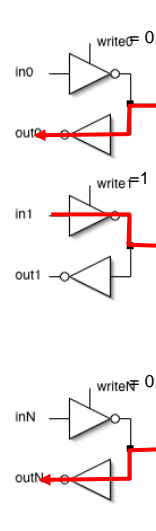


# Tri-state Buffers



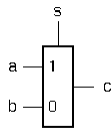
Tri-state buffers enable "bidirectional" connections.

Tri-state buffers are used when multiple circuits all connect to a common wire. Only one circuit at a time is allowed to drive the bus. All others "disconnect" their outputs, but can "listen".

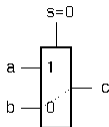
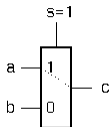


# Tri-state Based Multiplexor

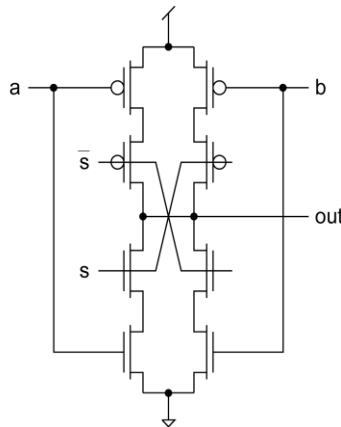
Multiplexor



If  $s=1$  then  $c=a$

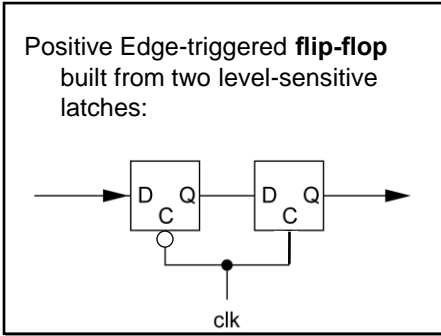
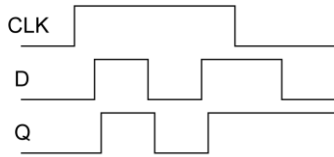
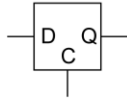


Transistor Circuit for inverting multiplexor:

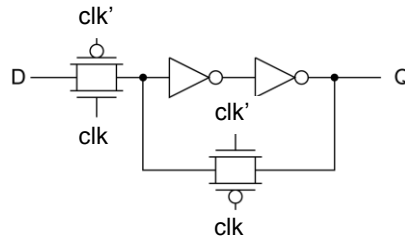


# Latches and Flip-flops

Positive level-sensitive latch:



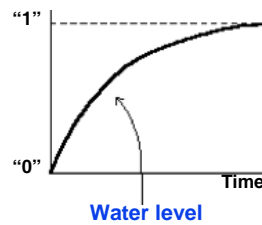
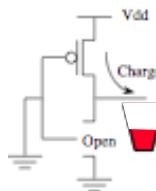
Latch Implementation:



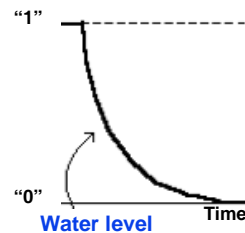
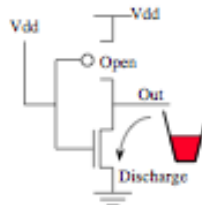
# CMOS Delay: Transistors as water valves

If electrons are water molecules,  
and a capacitor a bucket ...

A "on" p-FET fills up the capacitor with charge.



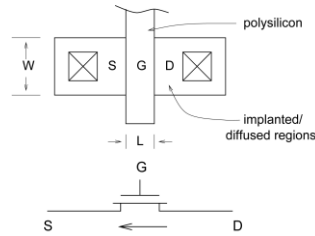
A "on" n-FET empties the bucket.



This model is often good enough

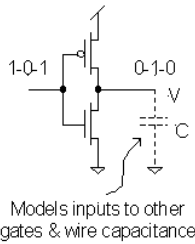
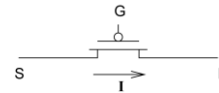
# Transistors as Conductors

- Improved Transistor Model: **nFET**



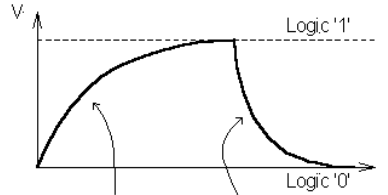
- We refer to transistor "strength" as the amount of current that flows for a given  $V_{ds}$  and  $V_{gs}$ .
- The strength is linearly proportional to the ratio of  $W/L$ .

## pFET



Fall 2013

Models inputs to other gates & wire capacitance

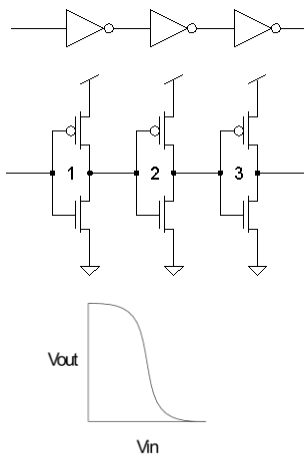


EECS150 - Lec20-CMOS

Page23

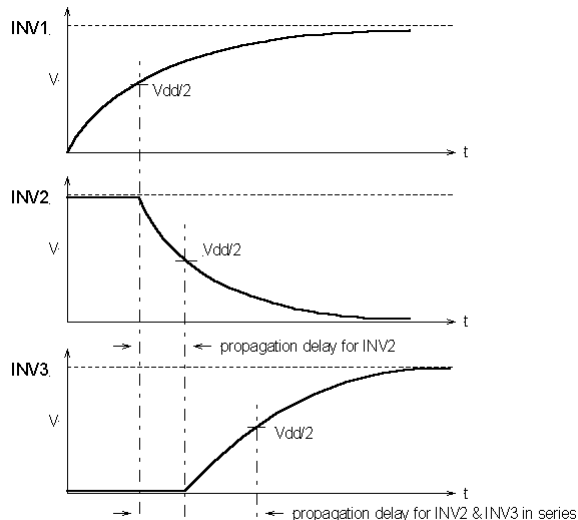
# Gate Delay is the Result of Cascading

- Cascaded gates:



"transfer curve" for inverter.

Fall 2013



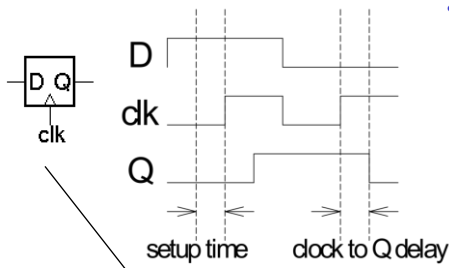
In general:

prop. delay = sum of individual prop. delays of gates in series.

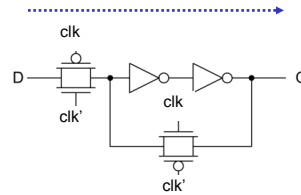
EECS150 - Lec20-CMOS

Page24

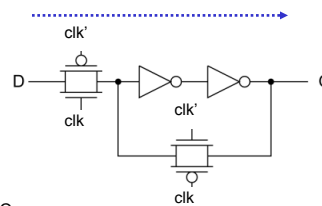
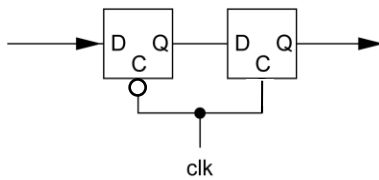
## Delay in Flip-flops



- Setup time results from delay through *first* latch.



• Clock to Q delay results from delay through *second* latch.

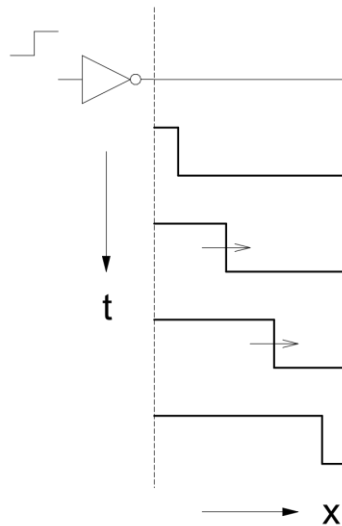


Fall 2013

EECS150 - Lec20-CMO~

Page 25

## Wire Delay



- Ideally, wires behave as “transmission lines”:
  - signal wave-front moves close to the speed of light
    - ~1ft/ns
  - Time from source to destination is called the “transit time”.
  - In ICs most wires are short, and the transit times are relatively short compared to the clock period and can be ignored.
  - Not so on PC boards.

Fall 2013

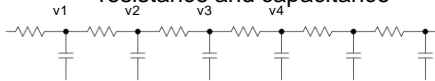
EECS150 - Lec20-CMOS

Page 26

## Wire Delay

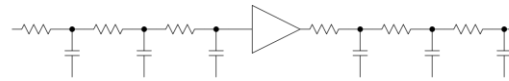
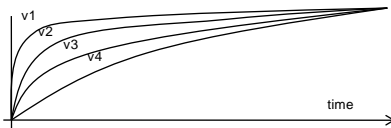
- Even in those cases where the transmission line effect is negligible:

- Wires possess distributed resistance and capacitance



- Time constant associated with distributed RC is proportional to the *square* of the length

- For **short wires** on ICs, resistance is insignificant (relative to effective R of transistors), but C is important.
  - Typically around half of C of gate load is in the wires.
- For **long wires** on ICs:
  - busses, clock lines, global control signal, etc.
  - Resistance is significant, therefore distributed RC effect dominates.
  - signals are typically “rebuffered” to reduce delay:

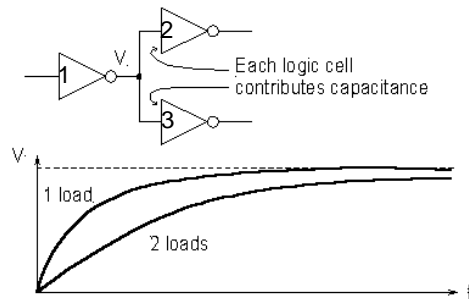


Fall 2013

EECS150 - Lec20-CMOS

Page27

## Delay and “Fan-out”



- The delay of a gate is proportional to its output capacitance. Connecting the output of a gate to more than one other gate increases its output capacitance. It takes increasingly longer for the output of a gate to reach the switching threshold of the gates it drives as we add more output connections.
- Driving wires also contributes to fan-out delay.
- What can be done to remedy this problem in large fan-out situations?

Fall 2013

EECS150 - Lec20-CMOS

Page28

## Conclusions

- CMOS details